

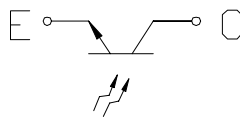
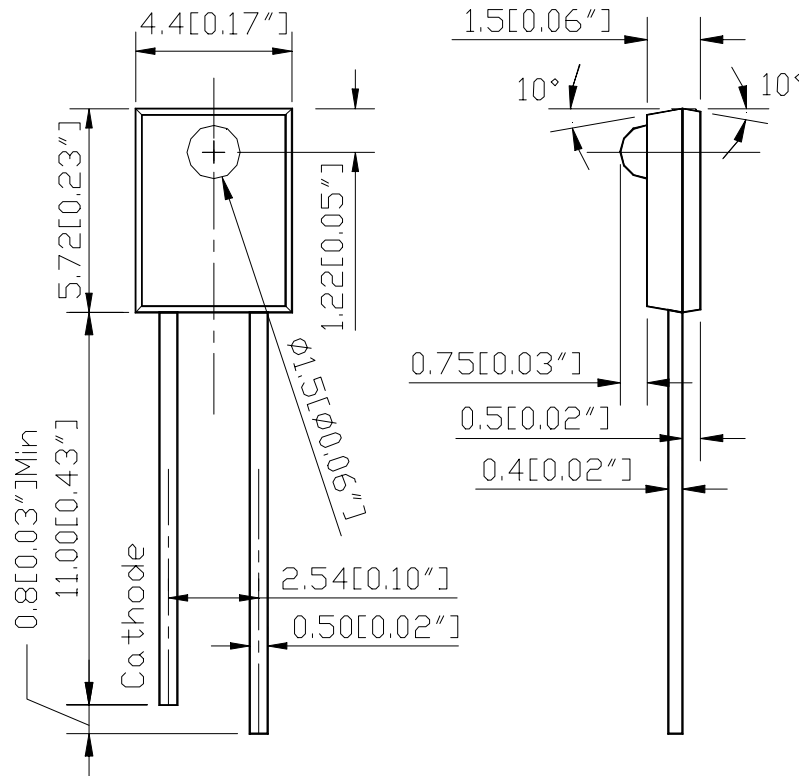
PHOTO TRANSISTOR

光電晶體

302 Photo Transistor Series

Part Number: TN2469TK

Package outlines



NOTES:

1. All dimensions are in millimeters (inches);
2. Tolerances are $\pm 0.2\text{mm}$ (0.008inch) unless otherwise noted.

ITEM	MATERIALS
Resin (mold)	Epoxy
Bonding wire	$\varnothing 30 \mu\text{m Au}$
Lens color	Water transparent
Dice	Silicon

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Part Number: TN2469TK

Absolute maximum ratings

($T_A=25^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Power dissipation	P_D	100	mW
Collector-emitter voltage	V_{CEO}	30	V
Emitter-collector voltage	V_{ECO}	5	V
Operating temperature range	T_{OP}	-20 ~+80	$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-20 ~+80	$^{\circ}\text{C}$
Lead soldering temperature	T_{SOL}	260 $^{\circ}\text{C}$ for 5 SEC (5mm [0.20"] from body)	

Electro-optical characteristics

($T_A=25^{\circ}\text{C}$)

Parameter	Test Condition	Symbol	Value			Unit
			Min	Typ	Max	
Collector-emitter breakdown voltage	$I_C = 100\mu\text{A}$ $I_B = 0$	$V_{(BR)CEO}$	30	--	--	V
Emitter-collector breakdown voltage	$I_E = 100\mu\text{A}$ $I_B = 0$	$V_{(BR)ECO}$	5	--	--	V
Collector-emitter saturation voltage	$I_C = 2\text{ mA}$ $I_B = 100\mu\text{A}$	$V_{CE(SAT)}$	--	--	0.3	V
Rise time	$V_{CE} = 5\text{V}$ $I_C = 1\text{ mA}$ $R_L = 1000\Omega$	T_R	--	15	--	μS
Fall time		T_F	--	15	--	μS
Collector dark current	$V_{CE} = 20\text{V}$ $E_e = 0\text{mW/cm}^2$	I_{CEO}	--	--	100	nA
On state collector current	$V_{CE} = 5\text{V}$ $E_e = 1\text{mW/cm}^2$ $\lambda = 940\text{nm}$	$I_{(ON)}$	0.20	1.0	--	mA